

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

OptiMOS™

OptiMOS™ 5 Power-Transistor, 150 V
BSC110N15NS5

Data Sheet

Rev. 2.1
Final

1 Description

Features

- N-channel, normal level
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- Very low on-resistance $R_{DS(on)}$
- 150 °C operating temperature
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC¹⁾ for target application
- Ideal for high-frequency switching and synchronous rectification

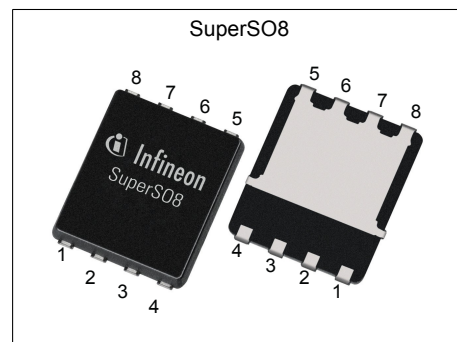
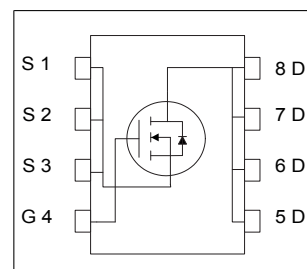


Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	150	V
$R_{DS(on),max}$	11	mΩ
I_D	76	A
Q_{OSS}	78	nC
$Q_G(0V..10V)$	28	nC
Q_{SW}	11.5	nC



Type / Ordering Code	Package	Marking	Related Links
BSC110N15NS5	PG-TDSON-8	110N15NS	-

¹⁾ J-STD20 and JESD22

Table of Contents

Description	2
Maximum ratings	4
Thermal characteristics	4
Electrical characteristics	5
Electrical characteristics diagrams	7
Package Outlines	11
Revision History	12
Disclaimer	12

2 Maximum ratings

at $T_j = 25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	76 48	A	$T_C=25\text{ °C}$ $T_C=100\text{ °C}$
Pulsed drain current ¹⁾	$I_{D,pulse}$	-	-	304	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ²⁾	E_{AS}	-	-	100	mJ	$I_D=50\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	125	W	$T_C=25\text{ °C}$
Operating and storage temperature	T_j, T_{stg}	-55	-	150	°C	IEC climatic category; DIN IEC 68-1: 55/150/56

3 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	0.6	1	K/W	-
Thermal resistance, junction - ambient, 6 cm ² cooling area ³⁾	R_{thJA}	-	-	50	K/W	-

¹⁾ See figure 3 for more detailed information

²⁾ See figure 13 for more detailed information

³⁾ Device on 40 mm x 40 mm x 1.5 mm epoxy PCB FR4 with 6 cm² (one layer, 70 µm thick) copper area for drain connection. PCB is vertical in still air.

4 Electrical characteristics

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	150	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	3	3.8	4.6	V	$V_{DS}=V_{GS}$, $I_D=91\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=25\text{ }^\circ\text{C}$ $V_{DS}=120\text{ V}$, $V_{GS}=0\text{ V}$, $T_J=125\text{ }^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	1	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	9 10	11 11.5	m Ω	$V_{GS}=10\text{ V}$, $I_D=38\text{ A}$, $V_{GS}=8\text{ V}$, $I_D=19\text{ A}$,
Gate resistance ¹⁾	R_G	-	0.9	1.35	Ω	-
Transconductance	g_{fs}	29	58	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=38\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance ¹⁾	C_{iss}	-	2080	2770	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Output capacitance ¹⁾	C_{oss}	-	515	685	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance ¹⁾	C_{rss}	-	13	23	pF	$V_{GS}=0\text{ V}$, $V_{DS}=75\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	10.3	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=38\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Rise time	t_r	-	3.3	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=38\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	14.5	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=38\text{ A}$, $R_{G,ext}=3\text{ }\Omega$
Fall time	t_f	-	2.9	-	ns	$V_{DD}=75\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=38\text{ A}$, $R_{G,ext}=3\text{ }\Omega$

Table 6 Gate charge characteristics²⁾

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	12	-	nC	$V_{DD}=75\text{ V}$, $I_D=38\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge ¹⁾	Q_{gd}	-	5.8	9	nC	$V_{DD}=75\text{ V}$, $I_D=38\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	11.5	-	nC	$V_{DD}=75\text{ V}$, $I_D=38\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total ¹⁾	Q_g	-	28	35	nC	$V_{DD}=75\text{ V}$, $I_D=38\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	5.8	-	V	$V_{DD}=75\text{ V}$, $I_D=38\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge ¹⁾	Q_{oss}	-	78	103	nC	$V_{DD}=75\text{ V}$, $V_{GS}=0\text{ V}$

¹⁾ Defined by design. Not subject to production test

²⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	76	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	304	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	0.88	1.2	V	$V_{GS}=0\text{ V}$, $I_F=38\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time ¹⁾	t_{rr}	-	45	90	ns	$V_R=75\text{ V}$, $I_F=38\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge ¹⁾	Q_{rr}	-	46	92	nC	$V_R=75\text{ V}$, $I_F=38\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$

¹⁾ Defined by design. Not subject to production test

5 Electrical characteristics diagrams

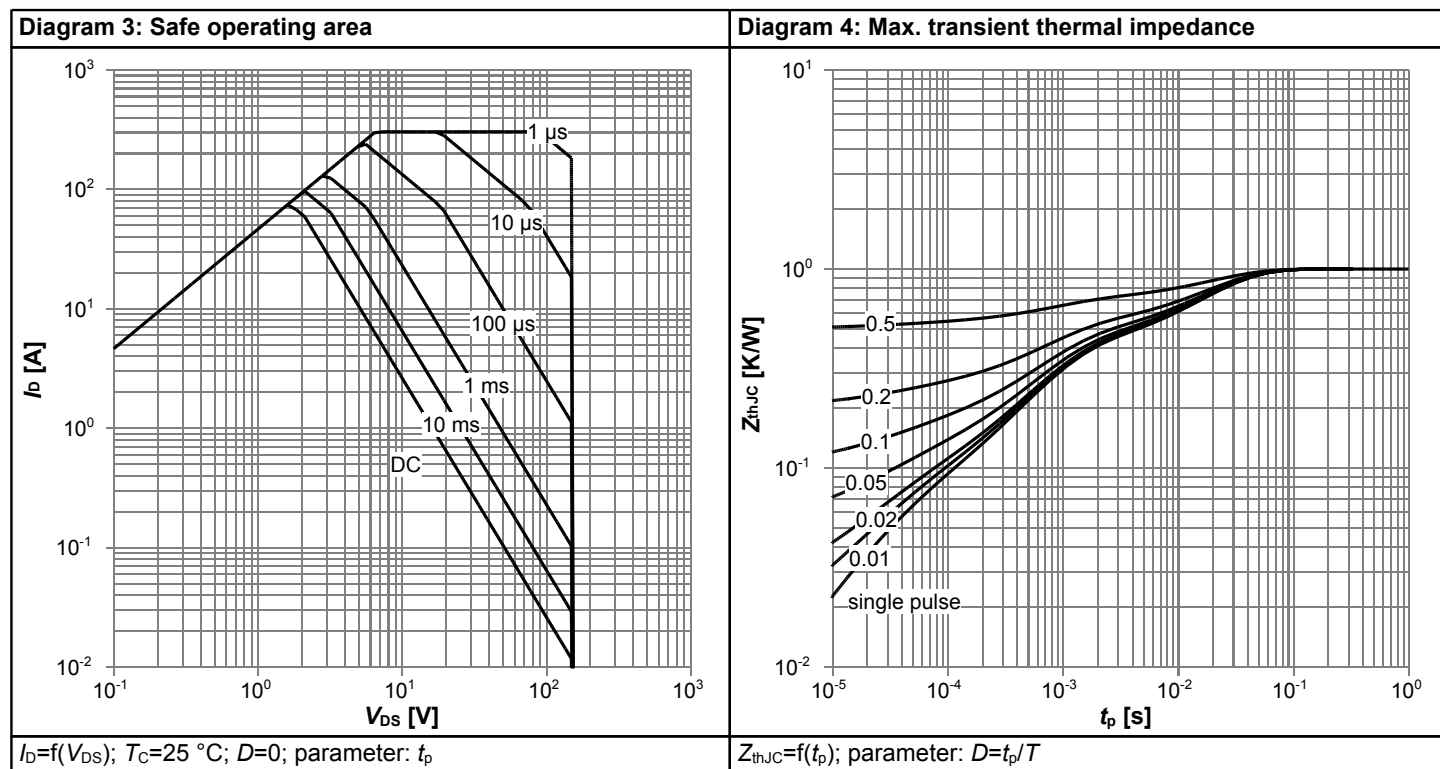
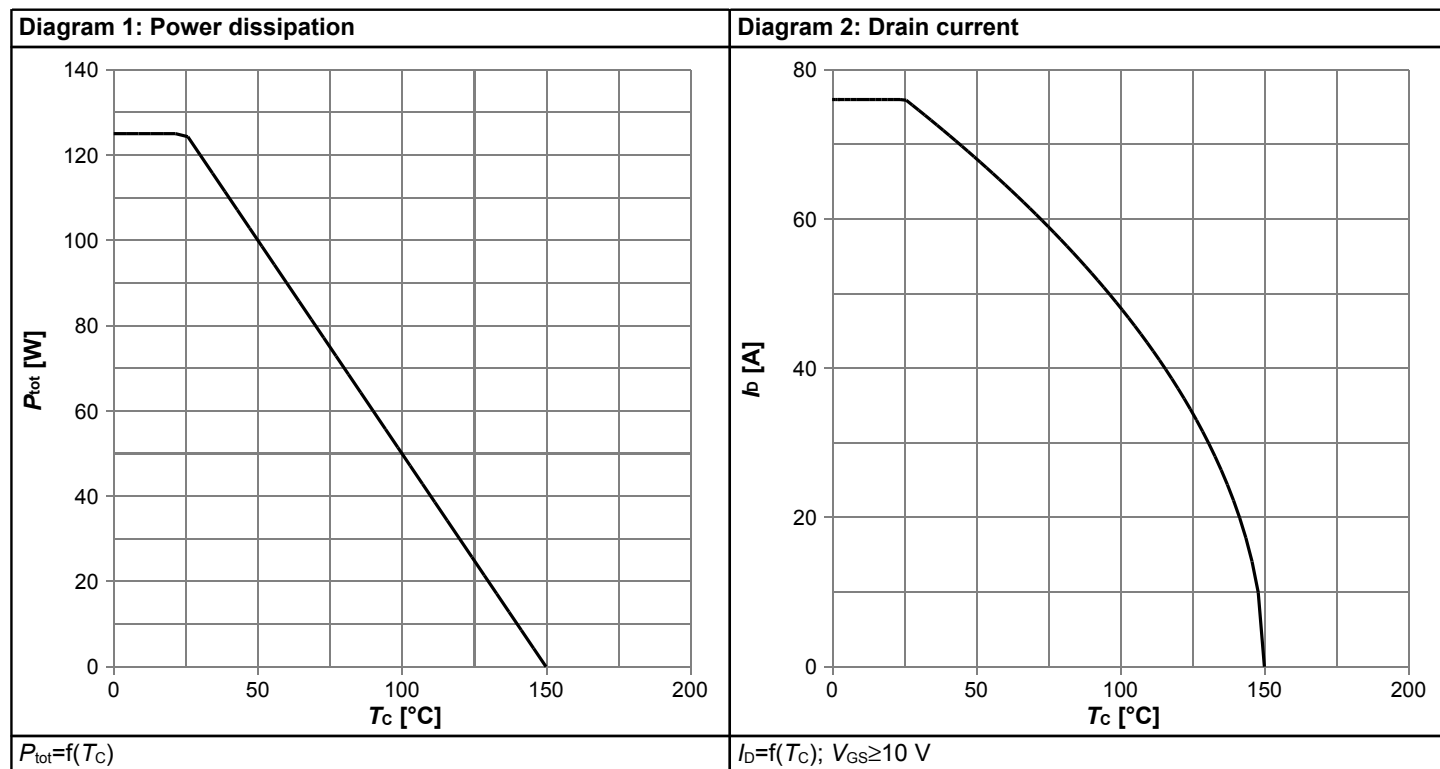


Diagram 5: Typ. output characteristics

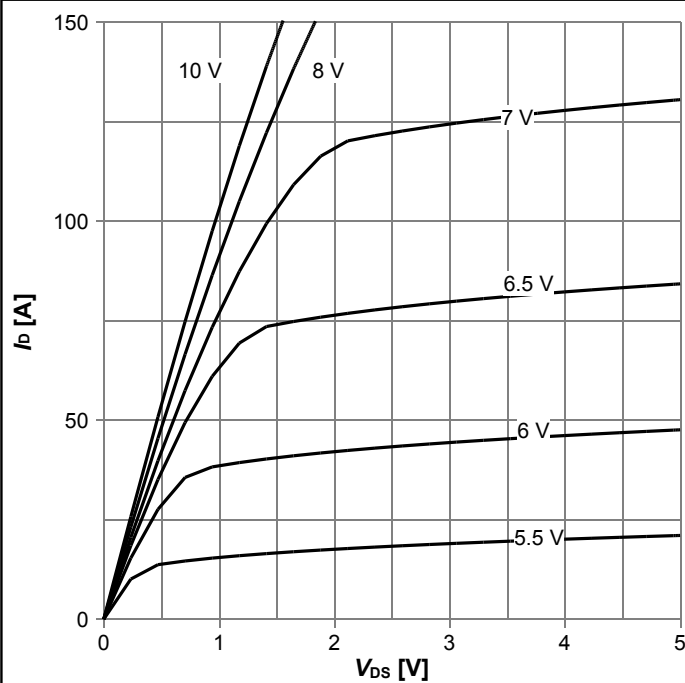

 $I_D = f(V_{DS}); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 6: Typ. drain-source on resistance

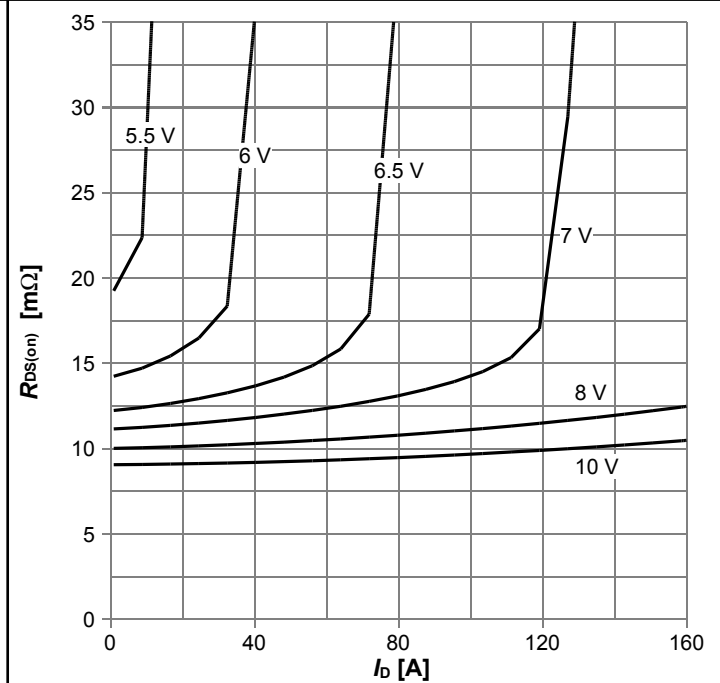

 $R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}; \text{parameter: } V_{GS}$

Diagram 7: Typ. transfer characteristics

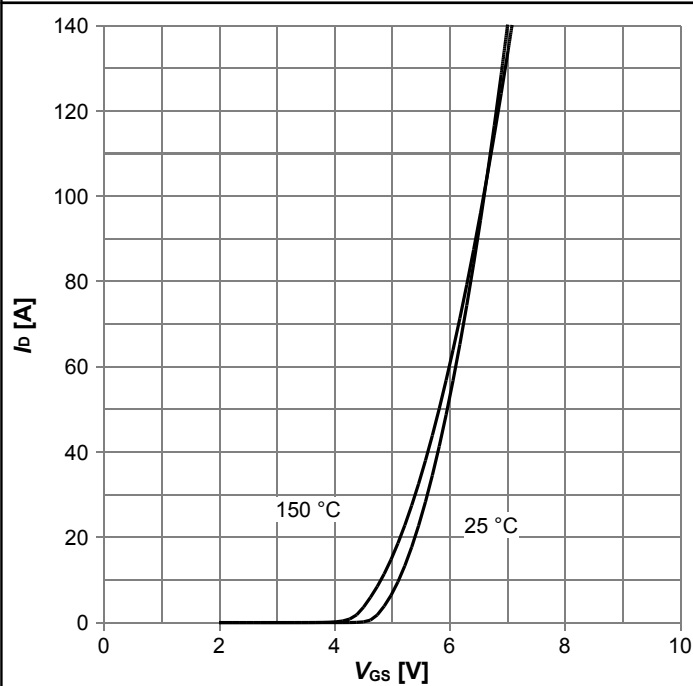

 $I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}; \text{parameter: } T_j$

Diagram 8: Typ. forward transconductance

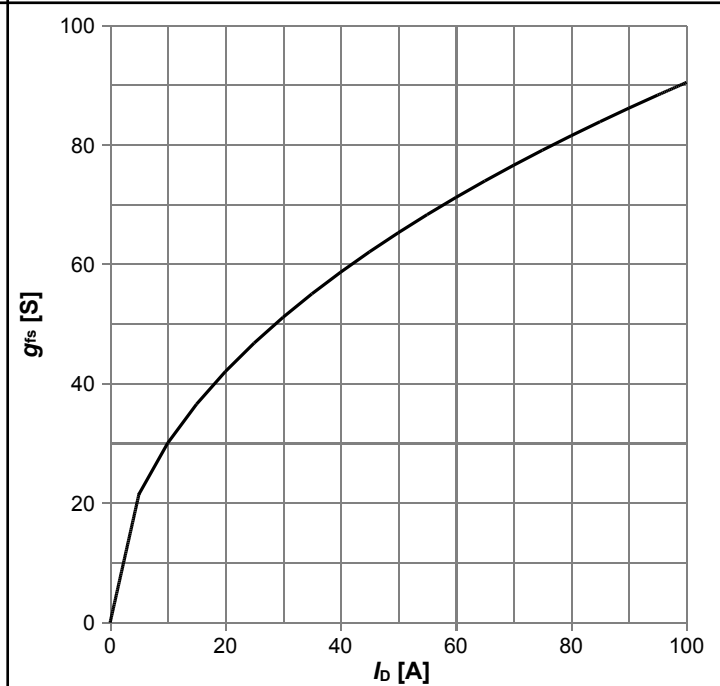
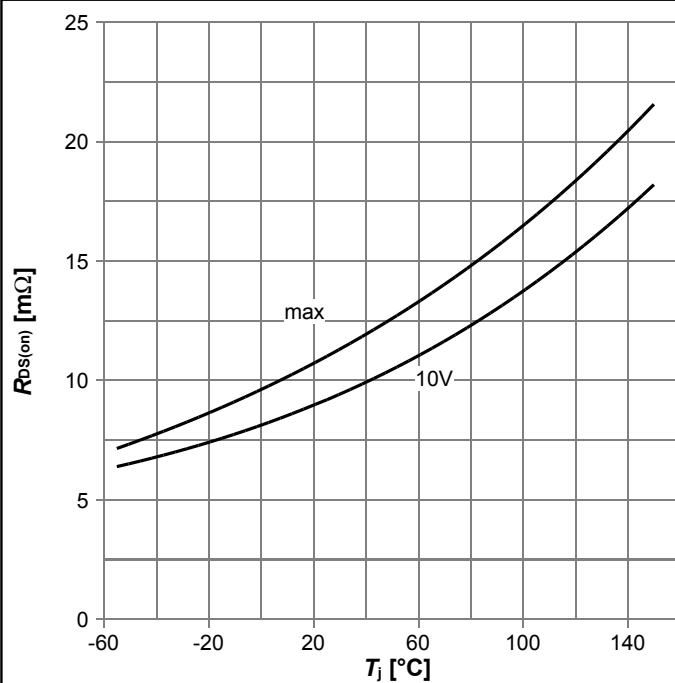
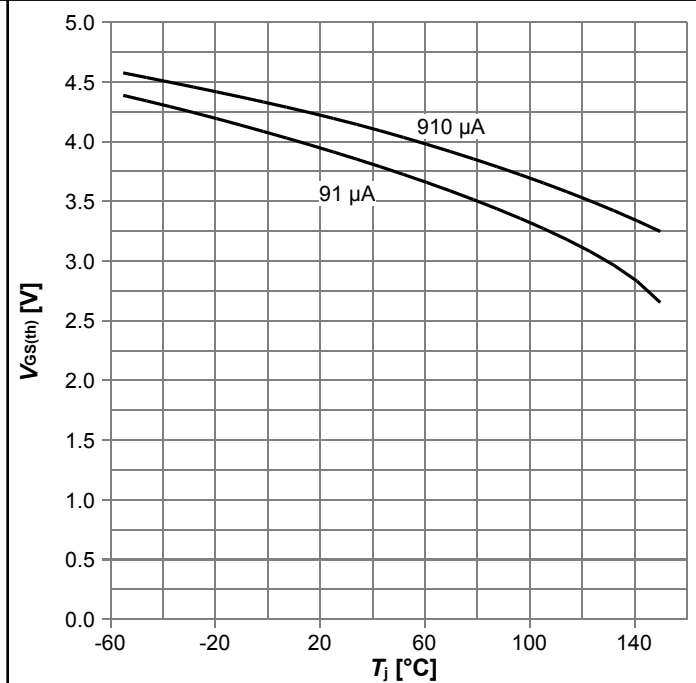

 $g_{fs} = f(I_D); T_j = 25^\circ\text{C}$

Diagram 9: Drain-source on-state resistance



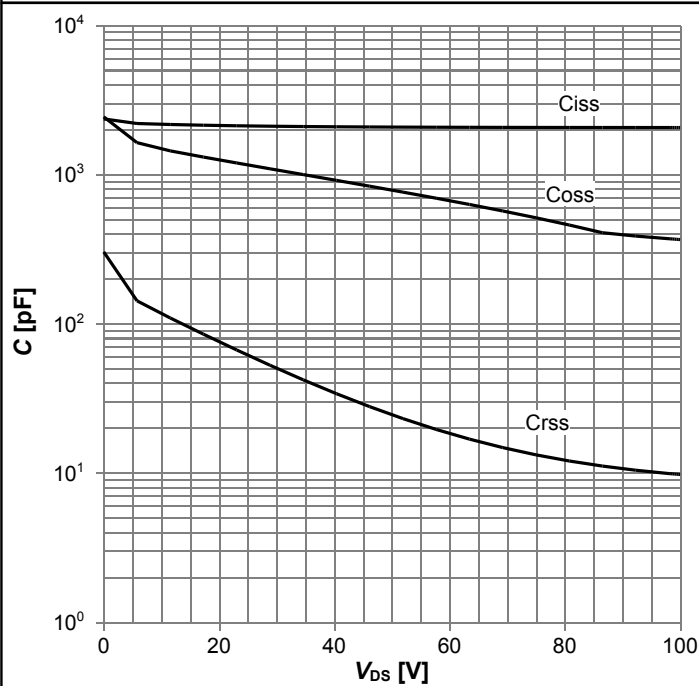
$$R_{DS(on)} = f(T_j); I_D = 38 \text{ A}; V_{GS} = 10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



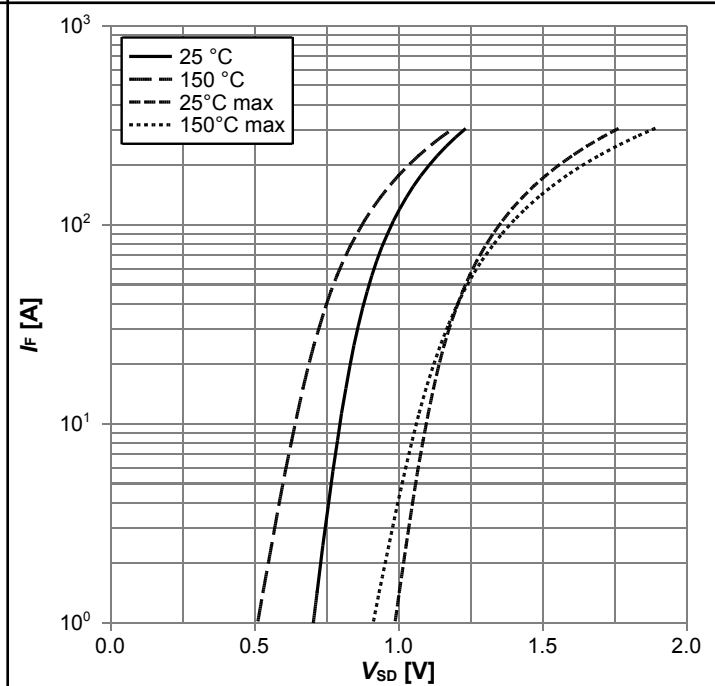
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; \text{parameter: } I_D$$

Diagram 11: Typ. capacitances



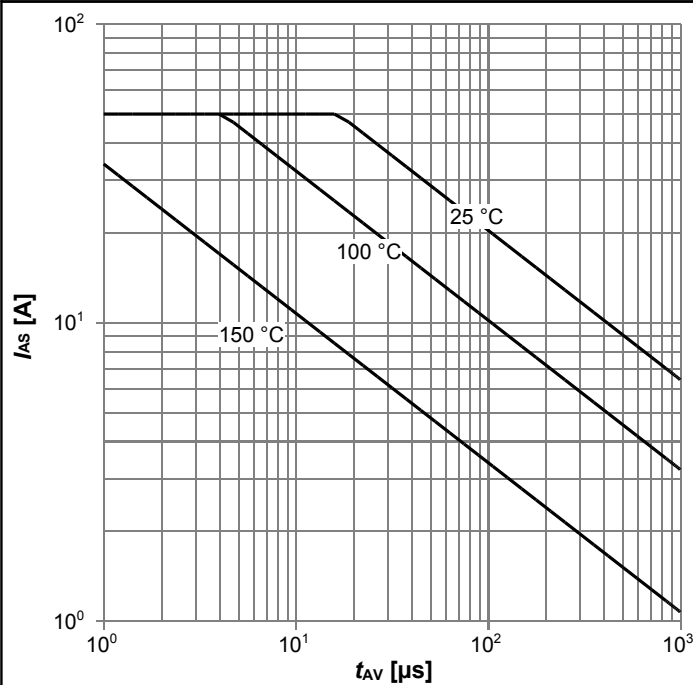
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Forward characteristics of reverse diode



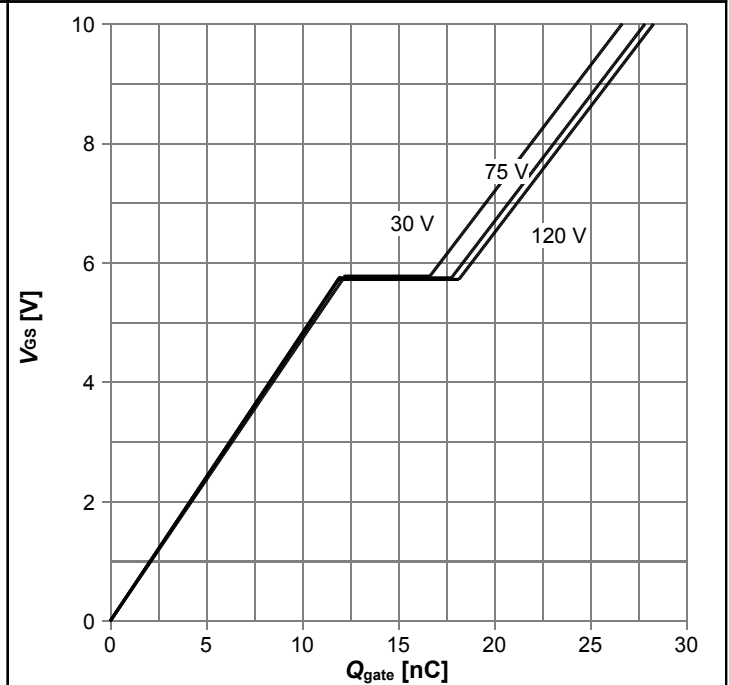
$$I_F = f(V_{SD}); \text{parameter: } T_j$$

Diagram 13: Avalanche characteristics



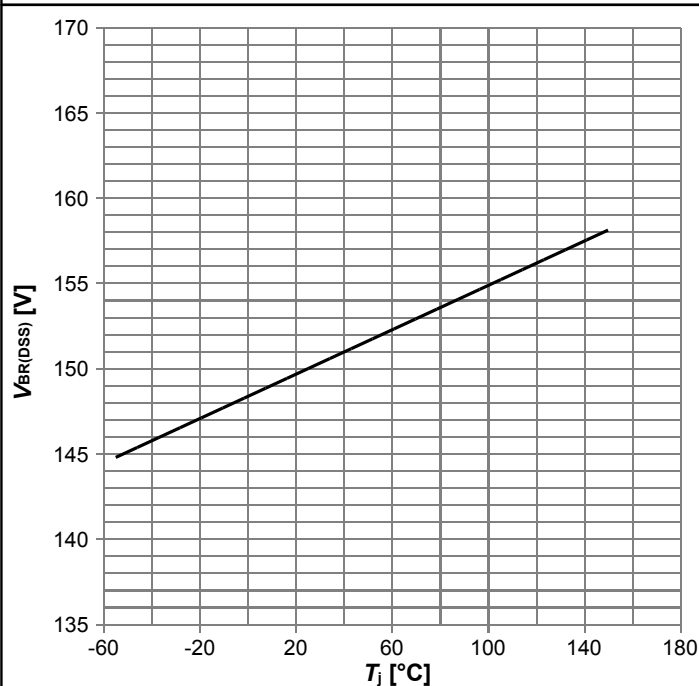
$$I_{AS}=f(t_{AV}); R_{GS}=25\ \Omega; \text{parameter: } T_{j(\text{start})}$$

Diagram 14: Typ. gate charge



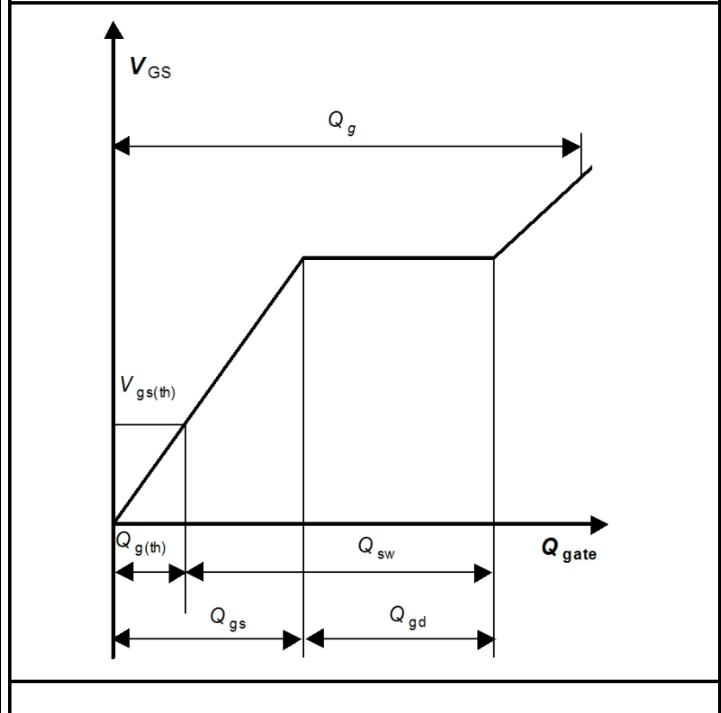
$$V_{GS}=f(Q_{\text{gate}}); I_D=38\text{A pulsed}; \text{parameter: } V_{DD}$$

Diagram 15: Drain-source breakdown voltage

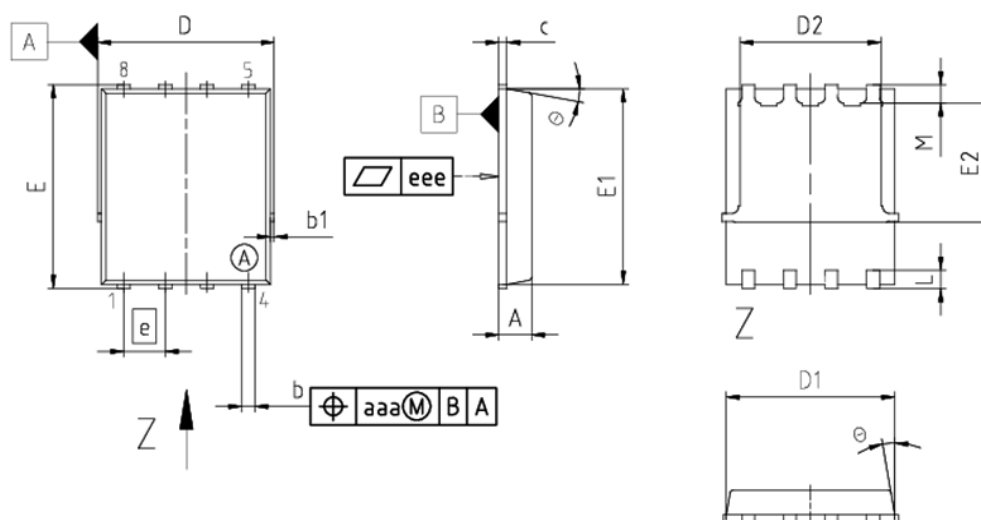


$$V_{BR(DSS)}=f(T_J); I_D=1\text{ mA}$$

Gate charge waveforms



6 Package Outlines



DIM	MILLIMETERS	
	MIN	MAX
A	0.90	1.10
b	0.31	0.54
b1	0.02	0.22
c	0.15	0.35
D	5.15	5.49
D1	4.95	5.35
D2	3.70	4.40
E	5.95	6.35
E1	5.70	6.10
E2	3.40	3.80
e	1.27	
N	8	
L	0.45	0.71
M	0.45	0.75
ø	8.5°	12°
aaa	0.25	
eee	0.08	

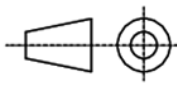
DOCUMENT NO. Z8B00003332
SCALE 0 2 4mm
EUROPEAN PROJECTION 
ISSUE DATE 10-04-2013
REVISION 04

Figure 1 Outline PG-TDSON-8, dimensions in mm

Revision History

BSC110N15NS5

Revision: 2015-06-09, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2015-05-26	Release of final version
2.1	2015-06-09	Update Avalanche Energy

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